Stabilization of competing ferroelectric phases of HfO$_2$ under epitaxial strain

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Hafnia (HfO$_2$)–based thin films have promising applications in nanoscale electronic devices due to their robust ferroelectricity and integration with silicon. However, HfO$_2$ has various stable and metastable polymorphs with quite similar structures and energies. Identifying and stabilizing the ferroelectric functional phases of HfO$_2$ have attracted intensive research interest in recent years. In this work, first–principles calculations on (111)–oriented HfO$_2$ are used to discover that imposing an in–plane shear strain on the tetragonal phase induces a nonpolar to polar phase transition. This in–plane shear–induced polar phase is shown to be an epitaxial distortion of a known metastable ferroelectric Pnma$_1$ phase of HfO$_2$. It is proposed that this ferroelectric Pnma$_1$ phase can account for the recently observed ferroelectricity in the (111)–oriented HfO$_2$–based thin film [Nature Materials 17, 1095–1100 (2018)]. Further investigation of this second functional ferroelectric phase in HfO$_2$ could potentially improve the performances of HfO$_2$–based films in logic and memory devices.

Ferroelectrics are materials with spontaneous electric polarization that can be switched by the application of an external electric field. This property makes ferroelectrics useful for a wide range of practical applications, such as non–volatile memory devices [1], field effect transistors [2], and tunable capacitors [3, 4]. However, most conventional ferroelectrics, such as BaTiO$_3$ or PbTiO$_3$, are not suitable for nanoscale devices, because of the depolarization field effect, which suppresses the ferroelectricity and becomes more significant as the thickness of films decreases [5–7]. HfO$_2$–based materials are exceptions; the Al [8], Gd [9], Sr [10], Y [11, 12] doped HfO$_2$ and Hf$_{0.5}$Zr$_{0.5}$O$_2$ alloy [13] can sustain ferroelectricity in films thinner than 20 nm. Furthermore, HfO$_2$–based materials can be integrated with silicon processing, and indeed are currently used as gate dielectrics [1, 14, 15].

HfO$_2$ adopts various polymorphs [10, 16] (Fig. 1). The ferroelectricity in thin films has generally been attributed to the formation of the orthorhombic P2a21 phase (oIII–phase) [17, 19]. The formation of the Pca2$_1$ phase is affected by various extrinsic factors, such as pressure [16], strain [20, 21], dopants [22, 23], oxygen vacancies [27], surface energies [24, 20] and electric fields [20, 31, 32]. This attribution does not preclude the existence of other competing ferroelectric phases [10]. For example, a ferroelectric phase different from oIII has been experimentally observed in (111)–oriented Hf$_{0.5}$Zr$_{0.5}$O$_2$ thin films [33]. This (111)–oriented ferroelectric film has a distinctive field–cycling behavior; wake–up cycling [10, 12] are not required for acquiring a steady P–E hysteresis loop. This intriguing observation invites a definitive identification of this novel phase, which should also provide a natural explanation for the lack of wake–up behavior and may be of great significance for practical applications of hafnia–based materials.

In this study, we carry out density–functional theory (DFT) based first–principles calculations on different polymorphs of HfO$_2$, with a particular focus on the ferroelectric orthorhombic Pnma$_1$ phase (oIV–phase). Although this oIV–phase is energetically less favorable in its conventional pseudocubic form [15], we provide evidence that it can be stabilized in epitaxial films with (111)–orientation via a transition from the tetragonal P4$_2$/nmc phase (t–phase), which has compatible lattice parameters for (111)–oriented crystals. In fact, the epitaxial geometry corresponding to a SrTiO$_3$ (001) substrate, the nonpolar t–phase is no longer locally stable, and collapses into a distorted version of the ferroelectric oIV phase, with a robust ferroelectric polarization ($P = 0.41$ C/m$^2$). Our simulated x–ray diffraction (XRD) for this phase is consistent with the one for the polar phase of Hf$_{0.5}$Zr$_{0.5}$O$_2$ experimentally reported in Ref. 33, suggesting new ferroelectric functionality for (111) films.

We performed first–principles calculations of the energies, structural parameters and polarization of various phases of HfO$_2$ using the QUANTUM–ESPRESSO [34] plane–wave DFT code within the local density approximation (LDA). To check the dynamical, elastic, and mechanical stability of the structures studied, we performed additional DFT calculations using the Projector Augmented Wave (PAW) method [35] as implemented in the VASP software [36, 38]. The numerical details along with the crystallographic information for the structures studied are provided in the supplemental material (SM) [59]. To understand the relationship between the tetragonal and the oIV phase, we start with the bulk t–phase of HfO$_2$ oriented along the (111) direction, with in–plane lattice parameters $a = 6.95$ Å, $b = 6.91$ Å, and cell angle $\gamma = 120^\circ$. We then apply an epitaxial strain of ~1% on the in–plane lattice constants to match those of the (111)–oriented oIV phase ($a = b = 7.01$ Å, $\gamma = 120^\circ$), and compute the potential energy profile as a function of the cell angle $\gamma$. We vary $\gamma$ in range $[110^\circ, 132^\circ]$, completely relax the distorted structures while fixing their in–plane lattice parameters ($a, b, \gamma$), corresponding to epitaxial constraint on a SrTiO$_3$ substrate, as explained in more detail below.
In Table I, we list the pseudocubic lattice parameters and relative energies for several widely reported phases of HfO$_2$. A schematic representation of the phase transitions among these phases is shown in Fig. 1(a). The bulk HfO$_2$ adopts a highly–symmetric $Fm\bar{3}m$ cubic fluorite structure (c–phase) at high temperatures ($T > 2773$ K), and transforms to the t–phase as temperature decreases ($2073 \text{ K} < T < 2773$ K). As the temperature drops below 2073 K, bulk HfO$_2$ transforms to a $P2_1/c$ monoclinic phase (m–phase) [40]. Our DFT calculations show that among these three phases, the c–phase has the highest energy and the m–phase has the lowest energy (see Table I), which is consistent with the experimental observations [40] and previous calculations. Doping is a well-known technique for stabilizing the t–phase in bulk [41]. In thin films, the large surface energy of the m–phase makes it less favorable [28–30]. As the thickness of the film decreases, the t–phase to m–phase transition temperature is suppressed, and in thin–enough films, the structure remains tetragonal at room temperature [42–44].

<table>
<thead>
<tr>
<th>phase</th>
<th>$a$</th>
<th>$b$</th>
<th>$c$</th>
<th>$\alpha$</th>
<th>$\beta$</th>
<th>$\gamma$</th>
<th>$\Delta E$</th>
</tr>
</thead>
<tbody>
<tr>
<td>$Fm\bar{3}m$ (c)</td>
<td>4.89</td>
<td>4.89</td>
<td>4.89</td>
<td>90.0</td>
<td>90.0</td>
<td>90.0</td>
<td>105.0</td>
</tr>
<tr>
<td>$P4_2/nmc$ (t)</td>
<td>4.89</td>
<td>4.89</td>
<td>4.93</td>
<td>90.0</td>
<td>90.0</td>
<td>90.0</td>
<td>80.2</td>
</tr>
<tr>
<td>$Pca2_1$ (oIII)</td>
<td>4.88</td>
<td>4.87</td>
<td>5.07</td>
<td>90.0</td>
<td>90.0</td>
<td>90.0</td>
<td>49.8</td>
</tr>
<tr>
<td>$P2_1/c$ (m)</td>
<td>5.06</td>
<td>4.93</td>
<td>5.05</td>
<td>90.0</td>
<td>90.0</td>
<td>99.3</td>
<td>0</td>
</tr>
<tr>
<td>$Pnm2_1$ (oIV)</td>
<td>4.95</td>
<td>4.95</td>
<td>4.96</td>
<td>90.0</td>
<td>90.0</td>
<td>83.9</td>
<td>110.2</td>
</tr>
</tbody>
</table>

TABLE I. Lattice parameters and relative energies ($\Delta E$) of different HfO$_2$ phases in their pseudocubic structures, corresponding to the conventional fcc cell of the $Fm\bar{3}m$ structure. Details of the cell transformations between the primitive cells and pseudocubic cells are provided in the SM. All length, angle, and energy units are in Å, degrees, and meV/f.u., respectively.

Recent experimental work demonstrates that the oIII ferroelectric phase forms as a compromise state resulting from the competition among bulk energy, surface, and doping energies [42, 45, 46], as shown in Fig. 1(a) and (b). Since the t– and oIII– phases have approximately identical in–plane lattice parameters (Table I), careful selection of film thickness, doping concentration and growth conditions is needed to stabilize this phase. For example, Böscke et al. proposed that depositing a top electrode before annealing can impose a mechanical confinement and promote the oIII–phase formation [17, 18].

Next, we consider the oIV–phase, which was proposed theoretically and investigated in previous work [16, 19], but has not yet been experimentally observed. The oIV–phase is also ferroelectric, being related to the tetragonal structure by the same polar distotion as the oIV–phase except along the (110) direction of the primitive tetragonal cell rather than the (100) direction. Our first–principles calculations based on the Berry’s phase method [27] reveal that this phase has a 0.59 C/m$^2$ polar-
ization along the [011] direction. The calculated phonon spectrum reveals that there are no unstable phonon modes in the oIV–phase, confirming the dynamical stability of this structure. Moreover, this structure is elastically and mechanically stable (see SM).

Our DFT results show that the relaxed bulk energy of the oIV–phase in (001)–oriented crystals is relatively high. As shown in Table I, the oIV–phase has the highest energy among the other studied phases. Besides, compared with the t–phase, which is the parent phase of other low–temperature phases, this ferroelectric phase has a more than 1% mismatch in the in–plane (a and b) lattices, and a difference of about 6° in the γ angle, making the t–phase to oIV–phase transition even more unfavorable for a square lattice epitaxial constraint in this plane.

However, the situation improves for the oIV–phase in (111)–oriented films. In Table II, we list the lattice parameters of (111)–oriented crystals of different HfO₂ phases. Among the low–temperature phases, the oIV–phase has the b lattice parameter closest to that of the t–phase. Besides, the difference in the angle γ decreases to less than 4°, which further increases the possibility of t–phase to oIV–phase transition. We also note that the major difference between the t– and oIV phases is in their γ angles, which inspires the investigation of whether a t–phase to oIV phase transition can be induced by modulating γ with a epitaxial shear strain.

<table>
<thead>
<tr>
<th>phase</th>
<th>a</th>
<th>b</th>
<th>c</th>
<th>α</th>
<th>β</th>
<th>γ</th>
</tr>
</thead>
<tbody>
<tr>
<td>Fm3m</td>
<td>6.91</td>
<td>6.91</td>
<td>8.46</td>
<td>90.0</td>
<td>90.0</td>
<td>120.0</td>
</tr>
<tr>
<td>P4_2/nmc</td>
<td>6.95</td>
<td>6.95</td>
<td>8.49</td>
<td>89.6</td>
<td>90.4</td>
<td>120.3</td>
</tr>
<tr>
<td>Pca2_1</td>
<td>6.89</td>
<td>7.03</td>
<td>8.56</td>
<td>91.8</td>
<td>90.1</td>
<td>119.4</td>
</tr>
<tr>
<td>P2_1/c</td>
<td>7.06</td>
<td>7.15</td>
<td>9.14</td>
<td>93.6</td>
<td>87.5</td>
<td>125.9</td>
</tr>
<tr>
<td>Pnm2_1</td>
<td>7.01</td>
<td>7.01</td>
<td>8.89</td>
<td>89.7</td>
<td>92.4</td>
<td>123.7</td>
</tr>
</tbody>
</table>

TABLE II. Lattice parameters of different HfO₂ phases in their (111)–oriented structures. We note that there are similar structures whose epitaxial planes are (-111), (-11-1) and so on; for simplicity, these are not included in the list. Detailed lattice parameters and atomic positions are given in the SM [39]. All length and angles units are in Å and degrees, respectively.

To explore the possible reaction path, we start with the t–phase and γ = 120° [Fig. 2(c)], since the t–phase is the parent phase of the low temperature phases. We then apply a ∼1% epitaxial strain on the in–plane lattices to match those of the (111)–oriented oIV phase (a = b = 7.01 Å, γ = 120°). Next, the γ angle is increased/decreased to 130°/110° with 1° steps. The energy and out–of–plane polarization are plotted as functions of γ in Fig. 2(a). We can see that as γ increases, a first–order phase transition occurs at γ = 128°, associated with a jump in the polarization [Fig 2(a), indicated by the black arrow]. The polar structure at γ = 129° is shown in Fig 2(d). Then we carry out a variable–cell relaxation about the polar structure, and find that the optimized structure is exactly the (111)–oriented oIV–structure. We also note that in the γ > 123° range, the distorted oIV–structure is energetically more favorable than the t–phase, indicating that the skew angle for triggering the phase transition can be as small as 3°. Meanwhile, decreasing γ to less than 114° also induces a first–order phase transition. The low–angle phase is also the oIV phase, but with a different epitaxial plane [(-11-1) oriented, Fig. 2(b)]. However, the polarization of this (-11-1)–oriented oIV structure lies in plane, which attracts less interest.

We have demonstrated that for (111)–oriented films, a t–phase to oIV phase transition can be induced by a shear strain [the schematic phase diagram is shown in Fig. 1(c)]. Such transitions are not uncommon when the underlying substrate has a different symmetry than that of the mounted thin film above. Based on these results, we propose a new ferroelectric phase stabilization process. At first, a (111)–oriented thin film is deposited on the substrate at a high temperature (> 1000 K). At this stage, a cubic or tetragonal structure is more favorable due to the surface energy and thermal budget. However, because of the lattice mismatch, the substrate keeps imposing a shear strain upon the film. After annealing,
the t–phase loses its stability, and collapses into the oIV ferroelectric phase.

Next, we consider the wake–up effect, which is the need for electric field cycling to establish the full value of switching polarization in as-grown thin films [10] [12]. This wake–up effect has a variety of origins, including internal bias fields [45] [46], migration of oxygen vacancies [15] [51], structural change at the interface [10] [45] [52]. An important intrinsic factor that can lead to a wake–up effect is an electric field induced non–polar to polar phase transition [10] [28] [53] [54]. In the [001]–oriented HfO_{2}–based films, the t–, oIII–, and m–phases are all metastable, indicating that all three states (or any two of them) can co–exist in an annealed film [16] [53]. In thin films with mixed t and oIII structures, electric field cycling can transform the non–polar t–phase into the ferroelectric oIII phase, producing a wake–up effect. However, in the (111)–oriented films, if the axis skew angle is larger than 8°, there is no admixture of nonpolar t–phase as it is unstable to the ferroelectric oIV phase. This can account for the observed reduction in wake–up effect in (111)–oriented films.

Further, this work suggests a structure for the experimentally reported ferroelectric phase in (111)–oriented Hf_{0.5}Zr_{0.5}O_{2} (HZO) films distinct from the rhombohedral structure previously proposed [33] [50]. In experiments, the deposition temperature is T = 800°C, which favors the non–polar t–phase. After annealing, thin films with robust polarization (0.34 C/m² for 5 nm and 0.18 C/m² for 9 nm) were obtained. This ferroelectricity can be attributed to the oIV phase. In our DFT calculation, the out–of plane polarization of (111)–oriented oIV phase is 0.41 C/m². It is not surprising that this value is somewhat larger than the experimentally reported results [33], since we consider a perfect polar oIV–phase in our calculations while the actual thin-films in experiments may contain some or a mixture of the nonpolar crystallites in a part, such as the m–phase. The size of the nonpolar crystallites grows with increasing film thickness, reducing the net polarization in the thicker films. The substitution of Hf by Zr may also contribute to a reduction in the polarization.

To estimate the shear strain imposed by the La_{0.7}Sr_{0.3}MnO_{3} (LSMO) substrate, we begin with analyzing the film–substrate geometry as shown in Fig. 3(a). Between the (001)–oriented LSMO substrate and (111)–oriented HZO thin film, there are several interfacial t–phase layers. Both LSMO and tetragonal HZO have a pseudocubic structure. However, their in–plane lattices are quite different (a_{HZO} = 5.06 Å and a_{LSMO} = 3.88 Å) [29] [57], and we do not expect a coherent strain. Here, we make the assumption that the effective lattice l is the average of a_{HZO} and a_{LSMO}. In Fig. 3(b), we plot the orientations of the crystalline axes with the experimental information [111]_{HZO}/[001]_{STO}, [1-10]_{HZO}/[1-10]_{STO}, and [11-2]_{HZO}/[110]_{STO}. For l = 1/2 (a_{HZO} + a_{LSMO}) = 4.47 Å, we have in–plane lattice parameters of the (111)–oriented films as l_a = l_b = 7.07 Å and γ = 127°, which is a remarkable match with our DFT predicted results.

In Fig. 4, we plot the simulated XRD patterns of the oIII and (111)–oriented oIV structures. Some XRD reflection peaks in the (111)–oriented oIV phase practically overlap.

FIG. 3. Schematic plots showing the (a) side view of thin–film geometry employed in Ref. [33], and (b) orientations of the crystalline axes. The dashed lines correspond to the [100]_{STO} and [010]_{STO} directions. The solid lines correspond to the [110]_{STO} and [1-10]_{STO} directions. The blue arrows labeled l_a and l_b correspond to the a and b axes of the (111)–oriented structure.

FIG. 4. Simulated XRD patterns of the oIII and (111)–oriented oIV structures. Some XRD reflection peaks in the (111)–oriented oIV phase practically overlap.
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wake–up effect, which is undesirable for technological ap-
propose that by a proper selection of the substrate, the
is metastable and has a robust polarization. We also
Pnm
roelectric

In this study, we predict a non–polar to polar phase
transition in (111)–oriented HfO2 from first-principles
calculations. Under an in–plane shear strain which en-
larges the γ angle, the nonpolar P42/nmc t–phase trans-
forms to a polar phase which is a distortion of the fer-
roelectric Pnrm, oIV–phase. This ferroelectric phase is
metastable and has a robust polarization. We also
propose that by a proper selection of the substrate, the
wake–up effect, which is undesirable for technological ap-
lications, can be reduced or eliminated, so that as-grown
films would be ferroelectric. Our work also opens a new
avenue to explaining the recent experimentally reported
ferroelectricity in (111)–oriented Hf0.5Zr0.5O2 thin films.

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[39] “See Supplemental Material (SM) at href for information regarding the numerical details, calculated phonon spectrum, elastic and mechanical properties, potential energy barrier profile for the oIII phase as a function of cell angle γ, and crystallographic details of the studied structures. SM consists Refs. [34–38, 60–64].”


[56] Our DFT calculations show that replacing half of the Hf atoms with Zr one does not affect the lattice parameters and relative energies very much.


